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TERMS, DEFINITIONS, ABBREVIATIONS,

SYMBOLS AND UNITS FOR

CHARGE COUPLED DEVICES

ESCC Basic Specification No. 2139020

Issue 3 Nove	ember 2013
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DOCUMENTATION CHANGE NOTICE

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1 <u>SCOPE</u>

This specification forms part of ESCC Basic Specification No. 21300 and covers Charge Coupled Devices.

2 TERMS, DEFINITIONS AND SYMBOL LETTERS

Symbol	Parameter
А	Pixel Area
a _i	Photoresponse Non-Uniformity or Dark Signal Limit for Number of Photoresponse Non-Uniformity or Dark Signal Defects
C _{ΦL,} C _{ΦM} C _{ΦP,} C _{ΦR}	Electrode Capacitance (for Readout Register, Memory Zone, Image Zone and Reset respectively)
$\begin{array}{c} C_{\Phi L_{0,}} C_{\Phi M_{0}} \\ C_{\Phi P_{0,}} C_{\Phi R_{0}} \end{array}$	Electrode Capacitance with Respect to Another Clock (for Readout Register, Memory Zone, Image Zone and Reset respectively)
CTE	Charge Transfer Efficiency
CTF	Contrast Transfer Function
CTI	Charge Transfer Inefficiency
CVF	Charge to Voltage Conversion Factor
DSNU	Dark Signal Non-Uniformity
ΔU _{Ref}	Reference Voltage Error Band
ΔU _{Signal}	Signal Voltage Error Band
E	Exposure
EB1	Reference Level Error Band
EB ₂	Signal Level Error Band
3	Charge Transfer Inefficiency for One Stage
FI	Image Zone to Memory Zone and Memory Zone to Output Register Frequency
FL	Output Register and Reset Frequency
ΦL	Readout Register Clock
Φ _M	Memory Zone Clock
Φ _P	Image Zone Clock
Φ _{PS}	Photosite to Shift Register Transfer Clock
Φ _R	Reset Clock
Φτ	Transport Clock
HCTE	Horizontal Charge Transfer Efficiency
HCTI	Horizontal Charge Transfer Inefficiency
IDD	Power Supply Current
IE	Insulation Leakage Current Between Pins (Input Current)
Ін	Internal Driver Supply Current
IL	Leakage Current on Input Gates
I _{RD}	Signal Current in Reset Bias Electrode
L	Length of Image Plane

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Symbol	Parameter
λ	Wavelength
LE	Linearity Error
MTF	Modulation Transfer Function
Ndefi	Number of Photoresponse Non-Uniformity or Dark Signal Defects Beyond ai Limit
NS	Total Smearing Factor
Р	Flatness of Image Area
ρ	Pixel Pitch
PRNU	Photoresponse Non-Uniformity
QE	Quantum Efficiency
R	Responsitivity
R(Bi)	Spectral Responsitivity in Optical Band Bi
SPRNU	Spectral Photoresponse Non-Uniformity
TDi	Timing Diagram i
t _{D-Reset}	Reset Level Setting Time
t _{D-Signal}	Signal Level Setting Time
t _f	Fall Time
t _h	High Level Time
Ti	Integration/ Exposure Time
TILT	Parallelism between Image Plane and window
tı	Low Level Time
T _{op}	Operating Temperature
tr	Rise Time
T _{ref}	Reference Temperature
TRIG	Signal for Acquisition Start
T _{sol}	Soldering Temperature
T _{stg}	Storage Temperature Range
Tt	Duration of Vertical Transfer Period
t _{U-Ref}	Reference Level Duration
tu-Signal	Signal Level Duration
Tc	Capture Time Constant or Trapping State in a CCD Buried Channel
Те	Emission Time Constant of Trapping State in a CCD Buried Channel
Θ	Image Plane Orientation (Skew)
Va	Average Output Signal under Illumination
Vantiblooming	Antiblooming Voltage
VCTE	Vertical Charge Transfer Efficiency
VCTI	Vertical Charge Transfer Inefficiency
V _{DD}	Output Amplifier Drain Supply
V _{DS}	Average Dark Signal
V _{GS}	Register Output Gate Bias

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Symbol	Parameter
VINVERSION	Inversion Voltage
V _N	Temporal RMS Noise in Darkness
Voffset	Offset Voltage
Vos	Video Output Signal
Vr	Reference Voltage for Modulation Calculation
V _{RD}	Reset Bias
V _{REF}	DC Output Level
VRESET	Amplitude of Reset Feedthrough
Vs	Signal Voltage
VSAT	Saturation Output Voltage
Vss	Substrate Bias Voltage
V _{Video}	Video Voltage
W	Width of Image Plane
WOC	Spectral Range for Optical Coating on Window
WT	Window Thickness
Х	Position of First Pixel (Horizontal)
Y	Position of First Pixel (Vertical)
Z	Optical Distance between Image Plane and Window
Zs	Output Impedance

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